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<0.5 Ω CMOS, 1.65 V to 3.6 V, Quad SPST Switches

ADG811/ADG812/ADG813

FEATURES

0.5 Ω typical on resistance
0.8 Ω maximum on resistance at 125°C
1.65 V to 3.6 V operation

Automotive temperature range: -40°C to $+125^{\circ}\text{C}$ High current carrying capability: 300 mA continuous

Rail-to-rail switching operation Fast switching times: <25 ns Typical power consumption <0.1 µW

APPLICATIONS

Cellular phones
MP3 players
Power routing
Battery-powered systems
PCMCIA cards
Modems
Audio and video signal routing
Communications systems

GENERAL DESCRIPTION

The ADG811/ADG812/ADG813 are low voltage CMOS devices containing four independently selectable switches. These switches offer ultralow on resistance of less than 0.8 Ω over the full temperature range. The digital inputs can handle 1.8 V logic with a 2.7 V to 3.6 V supply.

These devices contain four independent single-pole/single-throw (SPST) switches. The ADG811 and ADG812 differ only in that the digital control logic is inverted. The ADG811 switches are turned on with a logic low on the appropriate control input, while a logic high is required to turn on the switches of the ADG812. The ADG813 contains two switches whose digital control logic is similar to the ADG811, while the logic is inverted on the other two switches.

Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. The ADG813 exhibits break-before-make switching action.

The ADG811/ADG812/ADG813 are fully specified for 3.3 V, 2.5 V, and 1.8 V supply operation. The ADG811 is available in a 16-lead TSSOP package and a 16-lead LFCSP package, and the ADG812/ADG813 are available in a 16-lead TSSOP package.

FUNCTIONAL BLOCK DIAGRAMS

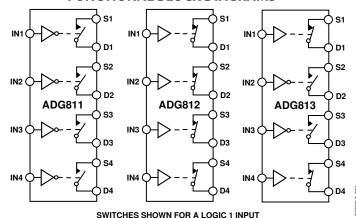


Figure 1.

PRODUCT HIGHLIGHTS

- 1. $< 0.8 \Omega$ over full temperature range of -40° C to $+125^{\circ}$ C.
- 2. Single 1.65 V to 3.6 V operation.
- 3. Operational with 1.8 V CMOS logic.
- 4. High current handling capability (300 mA continuous current at 3.3 V).
- 5. Low THD + N (0.02% typical).
- Small 3 mm × 3 mm LFCSP package and 16-lead TSSOP package.

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REVISION HISTORY

11/09—Rev. A to Rev. B	
Added 16-Lead LFCSP	Universa
Changes to Table 4	6
Changes to Pin Configurations and Function Descript	ion
Section	7
Moved Terminology Section	13
Updated Outline Dimensions	14
Changes to Ordering Guide	15

5/04—Rev. 0	to Rev.	A
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Updated Format	Universal
Updated Package Choices	Universal

11/03—Revision 0: Initial Version

SPECIFICATIONS

 $V_{\rm DD}$ = 2.7 V to 3.6 V, GND = 0 V, unless otherwise noted. Temperature range for the Y version is -40°C to +125°C.

Table 1.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V to V_{DD}$	٧	
On Resistance, R _{ON}	0.5			Ωtyp	$V_{DD} = 2.7 \text{ V}, V_S = 0 \text{ V to } V_{DD}, I_S = 10 \text{ mA}$
on nesistance, non	0.5			12 () [see Figure 19
	0.65	0.75	0.0	0	see rigule 19
	0.65	0.75	0.8	Ωmax	
On Resistance Match Between	0.04			Ω typ	$V_{DD} = 2.7 \text{ V}, V_S = 0.5 \text{ V}, I_S = 10 \text{ mA}$
Channels, ΔR_{ON}					
		0.075	0.08	Ω max	
On Resistance Flatness, R _{FLAT (ON)}	0.1			Ωtyp	$V_{DD} = 2.7 \text{ V}, V_S = 0 \text{ V to } V_{DD}, I_S = 10 \text{ mA}$
, , , , , , , , , , , , , , , , , , , ,		0.15	0.16	Ω max	, , , , , , , , , , , , , , , , , , , ,
LEAKAGE CURRENTS		0.13	0.10	12 max	$V_{DD} = 3.6 \text{ V}$
Source Off Leakage, I₅ (Off)	±0.2			nA typ	$V_S = 0.6 \text{ V}/3.3 \text{ V}, V_D = 3.3 \text{ V}/0.6 \text{ V};$
					see Figure 20
	±1	±8	±80	nA max	
Drain Off Leakage, I _D (Off)	±0.2			nA typ	$V_S = 0.6 \text{ V}/3.3 \text{ V}, V_D = 3.3 \text{ V}/0.6 \text{ V};$
					see Figure 20
	±1	±8	±80	nA max	_
Channel On Leakage, ID, Is (On)	±0.2	0		nA typ	$V_S = V_D = 0.6 \text{ V or } 3.3 \text{ V; see Figure } 21$
Charmer Off Leakage, ID, IS (Off)		. 4 =			vs = v ₀ = 0.0 v or 5.5 v, see rigure 21
	±1	±15	±90	nA max	
DIGITAL INPUTS					
Input High Voltage, VINH			2	V min	
Input Low Voltage, V _{INL}			0.8	V max	
Input Current, I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{INI}$ or V_{INH}
input current, time of time	0.003		.01		VIN — VINE OF VINH
			±0.1	μA max	
C _{IN} , Digital Input Capacitance	6			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	21			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	25	26	28	ns max	$V_S = 1.5 \text{ V/0 V}$; see Figure 22
t _{OFF}	4			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
COFF		6	7	7.	-
	5	6	7	ns max	V _s = 1.5 V; see Figure 22
Break-Before-Make Time Delay, t _{BBM}	17			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
(ADG813 Only)					
			5	ns min	$V_{S1} = V_{S2} = 1.5 \text{ V}$; see Figure 23
Charge Injection	30			pC typ	$V_S = 1.5 \text{ V, } R_S = 0 \Omega, C_L = 1 \text{ nF;}$
5 ,				' ' '	see Figure 24
Off Isolation	-67			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$;
On isolation	0,			ab typ	see Figure 25
Channel to Channel Constell	00			-ID +	
Channel-to-Channel Crosstalk	-90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$;
					see Figure 27
Total Harmonic Distortion (THD + N)	0.02			%	$R_L = 32 \Omega$, $f = 20 Hz$ to 20 kHz,
]	$V_S = 2 V p-p$
Insertion Loss	-0.05			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$
–3 dB Bandwidth	90			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
C _s (Off)	30			pF typ	
C _D (Off)	35			pF typ	
C _D , C _s (On)	60			pF typ	
POWER REQUIREMENTS					$V_{DD} = 3.6 \text{ V}$
I_{DD}	0.003			μA typ	Digital inputs = 0 V or 3.6 V
		1.0	4	μA max	· .
	1		•	m, tillux	1

¹ Guaranteed by design, but not subject to production test.

 V_{DD} = 2.5 V \pm 0.2 V, GND = 0 V, unless otherwise noted. Temperature range for the Y version is -40° C to $+125^{\circ}$ C.

Table 2.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V to V_{DD}$	٧	
On Resistance, R _{ON}	0.65			Ωtyp	$V_{DD} = 2.3 \text{ V, } V_S = 0 \text{ V to } V_{DD}, I_S = 10 \text{ mA}$
,				/ /	see Figure 19
	0.72	0.8	0.88	Ωmax	
On Resistance Match Between	0.04			Ωtyp	$V_{DD} = 2.3 \text{ V}, V_S = 0.55 \text{ V}, I_S = 10 \text{ mA}$
Channels, ∆R _{ON}				71	
		0.08	0.085	Ωmax	
On Resistance Flatness, RFLAT (ON)	0.16			Ωtyp	$V_{DD} = 2.3 \text{ V, } V_S = 0 \text{ V to } V_{DD}, I_S = 10 \text{ mA}$
, , ,		0.23	0.24	Ωmax	
LEAKAGE CURRENTS					$V_{DD} = 2.7 \text{ V}$
Source Off Leakage, Is (Off)	±0.2			nA typ	$V_S = 0.6 \text{ V}/2.4 \text{ V}, V_D = 2.4 \text{ V}/0.6 \text{ V};$
Jource on Leakage, is (Oir)	±0.2			пл сур	see Figure 20
	±1	±6	±35	nA max	seegae _s
Drain Off Leakage, I _D (Off)	±0.2	_0		nA typ	$V_S = 0.6 \text{ V}/2.4 \text{ V}, V_D = 2.4 \text{ V}/0.6 \text{ V};$
Drain On Leakage, ib (On)	±0.2			пл сур	see Figure 20
	±1	±6	±35	nA max	
Channel On Leakage, ID, Is (On)	±0.2	_0		nA typ	$V_S = V_D = 0.6 \text{ V or } 2.4 \text{ V}$; see Figure 21
Charmer on Ecakage, 15, 13 (on)	±1	±11	±70	nA max	v3 = vb = 0.0 v or 2.1 v, see rigare 21
DIGITAL INPUTS	<u> </u>	±11	170	IIA IIIda	
			1 7	\/i.a	
Input High Voltage, V _{INH}			1.7	V min	
Input Low Voltage, V _{INL}			0.7	V max	
Input Current, I _{INL} or I _{INH}	0.005			μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
			±0.1	μA max	
C _{IN} , Digital Input Capacitance	6			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	22			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	27	29	30	ns max	V _s = 1.5 V/ 0 V; see Figure 22
toff	4			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	6	7	8	ns max	$V_s = 1.5 V$; see Figure 22
Break-Before-Make Time Delay, tbbm	18			ns typ	$R_L = 50 \Omega, C_L = 35 pF$
(ADG813 Only)				, ,	
			5	ns min	$V_{S1} = V_{S2} = 1.5 \text{ V}$; see Figure 23
Charge Injection	25			pC typ	$V_S = 1.25 \text{ V, } R_S = 0 \Omega, C_L = 1 \text{ nF;}$
5 ,					see Figure 24
Off Isolation	-67			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$;
					see Figure 25
Channel-to-Channel Crosstalk	-90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$;
					see Figure 27
Total Harmonic Distortion (THD + N)	0.022			%	$R_L = 32 \Omega$, $f = 20 Hz$ to 20 kHz,
					$V_S = 1.5 \text{ V p-p}$
Insertion Loss	-0.06			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$
−3 dB Bandwidth	90			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
C _s (Off)	32			pF typ	
C _D (Off)	37			pF typ	
CD (O11)				pF typ	
	60			P. () P	
C _D , C _s (On)	60			P. 17P	$V_{DD} = 2.7 \text{ V}$
	0.003			μΑ typ	V _{DD} = 2.7 V Digital inputs = 0 V or 2.7 V

¹ Guaranteed by design, but not subject to production test.

 V_{DD} = 1.65 V to 1.95 V, GND = 0 V, unless otherwise noted. Temperature range for the Y version is -40°C to +125°C.

Table 3.

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0 V to V_{DD}$	V	
On Resistance, Ron	1			Ωtyp	$V_{DD} = 1.8 \text{ V}, V_S = 0 \text{ V to } V_{DD}, I_S = 10 \text{ mA};$ see Figure 19
	1.4	2.2	2.2	Ω max	
	2.5	4	4	Ω max	$V_{DD} = 1.65 \text{ V}, V_S = 0 \text{ V to } V_{DD}, I_S = 10 \text{ mA}$
On Resistance Match Between Channels, ΔR_{ON}	0.1			Ωtyp	$V_{DD} = 1.65 \text{ V}, V_S = 0.7 \text{ V}, I_S = 10 \text{ mA}$
LEAKAGE CURRENTS					V _{DD} = 1.95 V
Source Off Leakage Is (Off)	±0.2			nA typ	$V_S = 0.6 \text{ V}/1.65 \text{ V}, V_D = 1.65 \text{ V}/0.6 \text{ V};$ see Figure 20
	±1	±5	±30	nA max	
Drain Off Leakage I _D (Off)	±0.2			nA typ	$V_S = 0.6 \text{ V}/1.65 \text{ V}, V_D = 1.65 \text{ V}/0.6 \text{ V};$ see Figure 20
	±1	±5	±30	nA max	
Channel On Leakage ID, Is (On)	±0.2			nA typ	$V_S = V_D = 0.6 \text{ V or } 1.65 \text{ V; see Figure 21}$
	±1	±9	±60	nA max	
DIGITAL INPUTS					
Input High Voltage, V _{INH}			0.65V _{DD}	V min	
Input Low Voltage, V _{INL}			$0.35V_{DD}$	V max	
Input Current, I _{INL} or I _{INH}	0.005			μA typ	V _{IN} = V _{INL} or V _{INH}
·			±0.1	μA max	
CIN, Digital Input Capacitance	6			pF typ	
DYNAMIC CHARACTERISTICS ¹					
ton	27			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	35	36	37	ns max	V _s = 1.5 V/ 0 V; see Figure 22
toff	6			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
	8	9	10	ns max	V _s = 1.5 V; see Figure 22
Break-Before-Make Time Delay, t _{BBM} (ADG813 Only)	20			ns typ	$R_L = 50 \Omega$, $C_L = 35 pF$
•			5	ns min	$V_{S1} = V_{S2} = 1 \text{ V}$; see Figure 23
Charge Injection	15			pC typ	$V_S = 1 \text{ V, } R_S = 0 \Omega, C_L = 1 \text{ nF;}$ see Figure 24
Off Isolation	-67			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; Figure 25
Channel-to-Channel Crosstalk	-90			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$; see Figure 27
Total Harmonic Distortion (THD + N)	0.14			%	$R_L = 32 \Omega$, $f = 20 \text{ Hz to } 20 \text{ kHz}$, $V_S = 1.2 \text{ V p-p}$
Insertion Loss	-0.08			dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 kHz$
-3 dB Bandwidth	90			MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 26
C _s (Off)	32			pF typ	
C _D (Off)	38			pF typ	
C _D , C _s (On)	60			pF typ	
POWER REQUIREMENTS				· /·	V _{DD} = 1.95 V
• • • • • • • • • • • • • • • • • • •	0.003			μΑ typ	Digital inputs = 0 V or 1.95 V
I_{DD}	0.003			μιιγρ	

¹ Guaranteed by design, but not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 4.

	1 able 4.					
	Parameter	Rating				
•	V _{DD} to GND	-0.3 V to +4.6 V				
	Analog Inputs ¹	$-0.3 \text{ V to V}_{DD} + 0.3 \text{ V}$				
	Digital Inputs ¹	GND – 0.3 V to 4.6 V or				
		10 mA, whichever occurs first				
	Peak Current, S or D	(Pulsed at 1 ms, 10%				
		duty-cycle maximum)				
	3.3 V Operation	500 mA				
	2.5 V Operation	460 mA				
	1.8 V Operation	420 mA				
	Continuous Current, S or D					
	3.3 V Operation	300 mA				
	2.5 V Operation	275 mA				
	1.8 V Operation	250 mA				
	Operating Temperature Range,	−40°C to +125°C				
	Automotive (Y Version)					
	Storage Temperature Range	−65°C to +150°C				
	Junction Temperature	150℃				
	TSSOP Package					
	θ_{JA} Thermal Impedance	150°C/W				
	θ_{JC} Thermal Impedance	27°C/W				
	LFCSP Package					
	θ_{JA} Thermal Impedance	70°C/W				
	IR Reflow, Peak Temperature < 20 sec	235°C				

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

Table 5. ADG811/ADG812 Truth Table

ADG811 IN	ADG812 IN	Switch Condition
0	1	On
1	0	Off

Table 6. ADG813 Truth Table

Logic	Switch 1, Switch 4	Switch 2, Switch 3
0	Off	On
1	On	Off

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

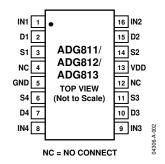


Figure 2. ADG811/ADG812/ADG813 Pin Configuration (16-Lead TSSOP)

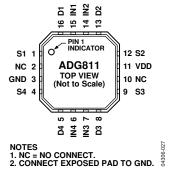


Figure 3. ADG811 Pin Configuration (16-Lead LFCSP)

Table 7. ADG811/ADG812/ADG813 Pin Configuration (16-Lead TSSOP)

(16-Lead TSSOP)				
Pin No.	Mnemonic	Definition		
1	IN1	Logic control input.		
2	D1	Drain Terminal. This pin may be an input or output.		
3	S1	Source Terminal. This pin may be an input or output.		
4	NC	No Connect.		
5	GND	Ground (0 V) reference.		
6	S4	Source Terminal. This pin may be an input or output.		
7	D4	Drain Terminal. This pin may be an input or output.		
8	IN4	Logic Control Input.		
9	IN3	Logic Control Input.		
10	D3	Drain Terminal. This pin may be an input or output.		
11	S3	Source Terminal. This pin may be an input or output.		
12	NC	No Connect.		
13	VDD	Most Positive Power Supply Potential.		
14	S2	Source Terminal. This pin may be an input or output.		
15	D2	Drain Terminal. This pin may be an input or output.		
16	IN2	Logic Control Input.		

Table 8. ADG811 Pin Configuration (16-Lead LFCSP)

Pin No.	Mnemonic	Definition			
1	S1				
1	31	Source Terminal. This pin may be an input or output.			
2	NC	No Connect.			
3	GND	Ground (0 V) Reference.			
4	S4	Source Terminal. This pin may be an input or output.			
5	D4	Drain Terminal. This pin may be an input or output.			
6	IN4	Logic Control Input.			
7	IN3	Logic Control Input.			
8	D3	Drain Terminal. This pin may be an input or output.			
9	S3	Source Terminal. This pin may be an input or output.			
10	NC	No Connect.			
11	VDD	Most Positive Power Supply Potential.			
12	S2	Source Terminal. This pin may be an input or output.			
13	D2	Drain Terminal. This pin may be an input or output.			
14	IN2	Logic Control Input.			
15	IN1	Logic Control Input.			
16	D1	Drain Terminal. This pin may be an input or output.			
	EPAD	Connect exposed pad to GND.			

TYPICAL PERFORMANCE CHARACTERISTICS

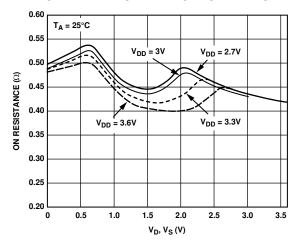


Figure 4. On Resistance vs. V_D (V_S), $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$

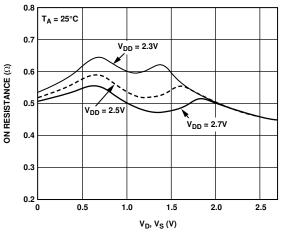


Figure 5. On Resistance vs. V_D (V_S), $V_{DD} = 2.5 V \pm 0.2 V$

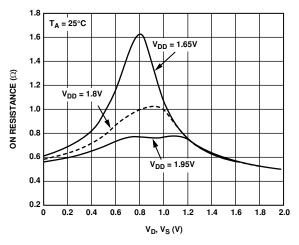


Figure 6. On Resistance vs. V_D (V_S), $V_{DD} = 1.8 \text{ V} \pm 0.15 \text{ V}$

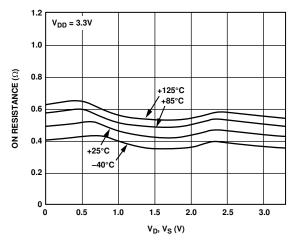


Figure 7. On Resistance vs. V_D (V_S) for Different Temperatures, $V_{DD} = 3.3 \text{ V}$

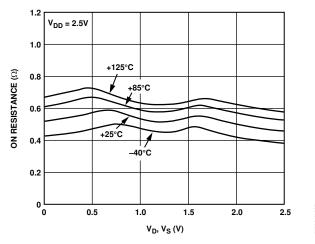


Figure 8. On Resistance vs. V_D (V_S) for Different Temperatures, $V_{DD} = 2.5 \text{ V}$

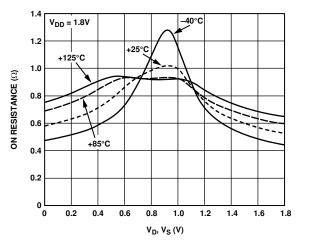


Figure 9. On Resistance vs. V_D (V_S) for Different Temperatures, $V_{DD} = 1.8 \text{ V}$

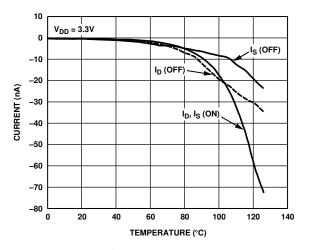


Figure 10. Leakage Current vs. Temperature, $V_{DD} = 3.3 \text{ V}$

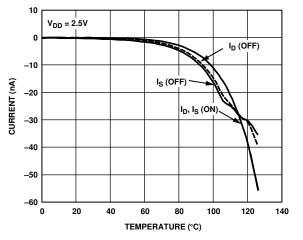


Figure 11. Leakage Current vs. Temperature, $V_{DD} = 2.5 V$

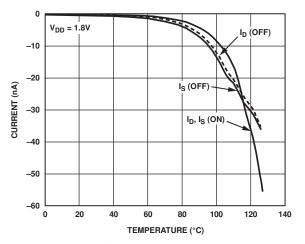


Figure 12. Leakage Current vs. Temperature, $V_{DD} = 1.8 \text{ V}$

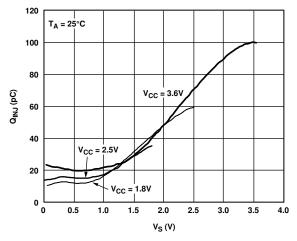


Figure 13. Charge Injection (Q_{INJ}) vs. Source Voltage (V_S)

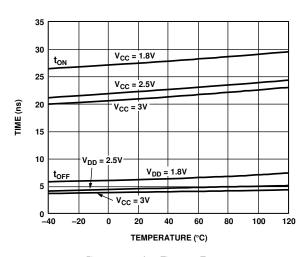


Figure 14. t_{ON}/t_{OFF} Times vs. Temperature

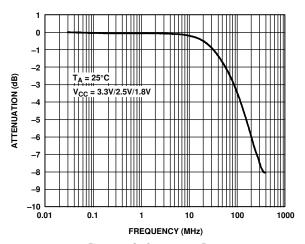


Figure 15. On Response vs. Frequency

04306-A-014

04306-A-013

04306-A-012

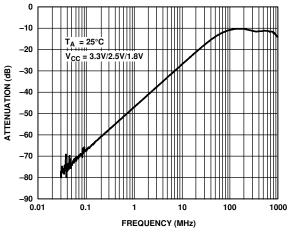


Figure 16. Crosstalk vs. Frequency

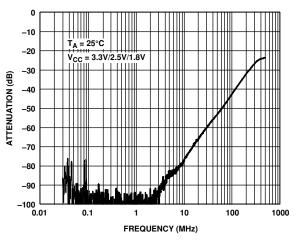


Figure 17. Off Isolation vs. Frequency

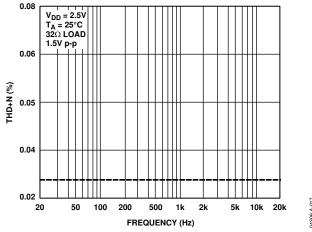
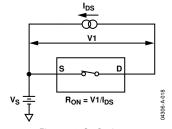
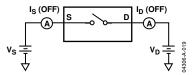


Figure 18. Total Harmonic Distortion + Noise (THD + N) vs. Frequency

TEST CIRCUITS





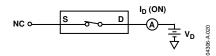


Figure 19. On Resistance

Figure 20. Off Leakage

Figure 21. On Leakage

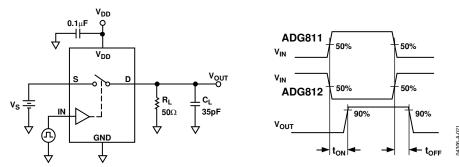


Figure 22. Switching Times

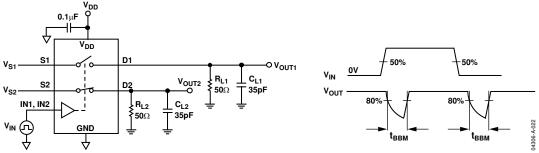


Figure 23. Break-Before-Make Time Delay, t_{BBM} (ADG813 Only)

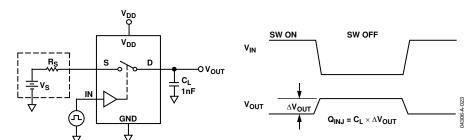


Figure 24. Charge Injection

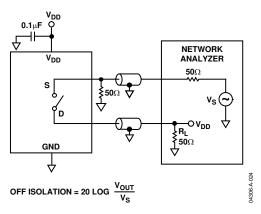


Figure 25. Off Isolation

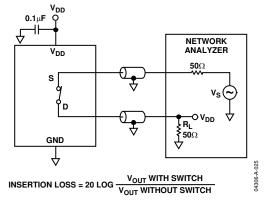


Figure 26. Bandwidth

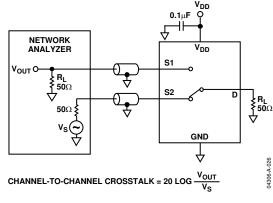


Figure 27. Channel-to-Channel Crosstalk

TERMINOLOGY

 I_{DD}

Positive supply current.

 V_D, V_S

Analog voltage on Terminal D, Terminal S.

Ros

Ohmic resistance between D and S.

R_{FLAT} (ON)

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

 ΔR_{ON}

On resistance match between any two channels, that is,

 R_{ON} maximum – R_{ON} minimum.

Is (Off)

Source leakage current with the switch off.

I_D (Off)

Drain leakage current with the switch off.

 I_D , I_S (On)

Channel leakage current with the switch on.

 V_{INL}

Maximum input voltage for Logic 0.

 V_{INH}

Minimum input voltage for Logic 1.

 $I_{INL}(I_{INH})$

Input current of the digital input.

Cs (Off)

Off switch source capacitance. Measured with reference to ground.

C_D (Off)

Off switch drain capacitance. Measured with reference to ground.

 C_D , C_S (On)

On switch capacitance. Measured with reference to ground.

 C_{IN}

Digital input capacitance.

ton

Delay time between the 50% and the 90% points of the digital input and switch on condition.

 t_{OFF}

Delay time between the 50% and the 90% points of the digital input and switch off condition.

 t_{BBM}

On or off time measured between the 80% points of both switches, when switching from one to another.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during on-to-off switching.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another because of parasitic capacitance.

-3 dB Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

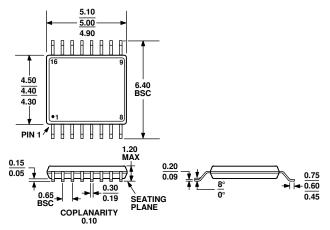
Insertion Loss

The loss due to the on resistance of the switch.

THD + N

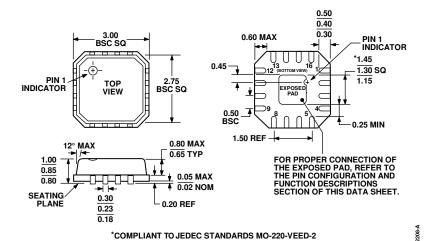
The ratio of the harmonic amplitudes plus noise of a signal to the fundamental.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 28. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16) Dimensions shown in millimeters



EXCEPT FOR EXPOSED PAD DIMENSION.

Figure 29. 16-Lead Lead Frame Chip Scale Package [LFCSP_VQ]

3 mm × 3 mm Body, Very Thin Quad

(CP-16-2)

Dimensions shown in millimeters

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ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	
ADG811YRU	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG811YRU-REEL	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG811YRU-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG811YRUZ ¹	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG811YCPZ-REEL ¹	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-16-2	
ADG811YCPZ-REEL71	-40°C to +125°C	16-Lead Lead Frame Chip Scale Package [LFCSP_VQ]	CP-16-2	
ADG812YRU	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG812YRU-REEL	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG812YRU-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG812YRUZ ¹	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG812YRUZ-REEL71	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG813YRU	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG813YRU-REEL	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG813YRU-REEL7	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	
ADG813YRUZ ¹	-40°C to +125°C	16-Lead Thin Shrink Small Outline [TSSOP]	RU-16	

 $^{^{1}}$ Z = RoHS Compliant Part.

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NOTES

